**Preferred Device** 

# One Watt Amplifier Transistor

## **PNP Silicon**

#### **Features**

• Pb-Free Package is Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-4.0	Vdc
Collector Current – Continuous	Ic	-500	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.0 8.0	W mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS

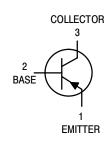
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



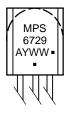
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#### **MARKING DIAGRAM**



MPS6729 = Device Code A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package
(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping
MPS6729	TO-92	5000 Units / Bulk
MPS6729G	TO-92 (Pb-Free)	5000 Units / Bulk

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector – Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	-80	_	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 0.1 mA, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	-80	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = -10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	-5.0	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -60 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	-0.1	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-10	μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ( $I_C = -50$ mAdc, $V_{CE} = -1.0$ Vdc) ( $I_C = -250$ mAdc, $V_{CE} = -1.0$ Vdc)	h <sub>FE</sub>	80 50	_ 250	_
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -250 mAdc, I <sub>B</sub> = -10 mAdc)	V <sub>CE(sat)</sub>	-	-0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -250 mAdc, V <sub>CE</sub> = -1.0 Vdc)	V <sub>BE(on)</sub>	-	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u> </u>			
Collector–Base Capacitance (V <sub>CB</sub> = -10 Vdc, f = 1.0 MHz)	C <sub>cb</sub>	_	30	pF
Small–Signal Current Gain (I <sub>C</sub> = 200 mA, V <sub>CE</sub> = 5.0 V, f = 20 MHz)	h <sub>fe</sub>	2.5	25	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

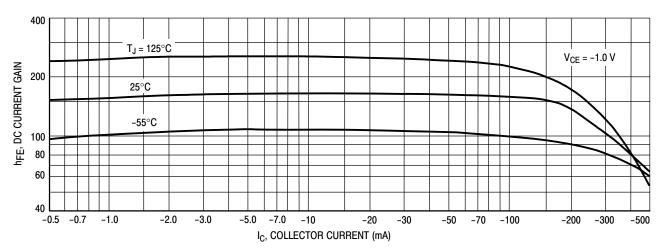


Figure 1. DC Current Gain

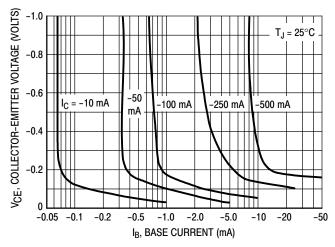


Figure 2. Collector Saturation Region

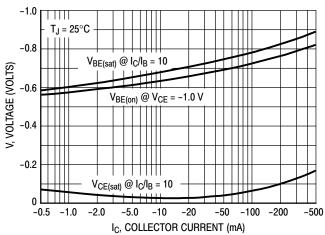


Figure 3. "On" Voltages

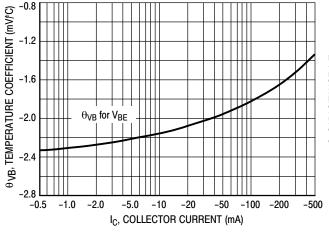


Figure 4. Base-Emitter Temperature Coefficient

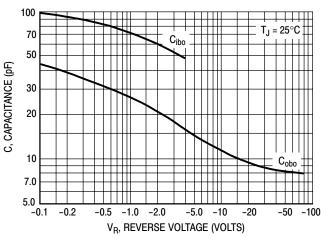


Figure 5. Capacitance

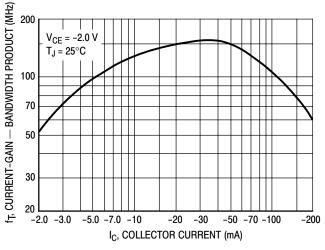


Figure 6. Current-Gain - Bandwidth Product

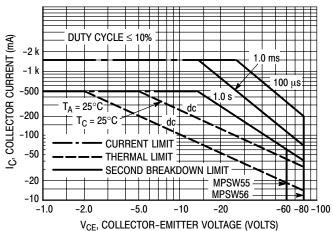
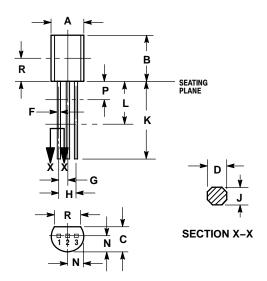


Figure 7. Active Region - Safe Operating Area

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-10 ISSUE AL



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- 4. DIMENSION F APPLIES BETWEEN P AND L
  DIMENSIONS D AND J APPLY BETWEEN L AND K
  MIMIMUM. LEAD DIMENSION IS UNCONTROLLED
  IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0 135		3 43	

STYLE 1: PIN 1. EMITTER

11. EMITTER 2. BASE

3. COLLECTOR

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